

MMBT4403WT1G

Switching Transistor

PNP Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating: Human Body Model; 4 kV,
Machine Model; 400 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-40	Vdc
Collector - Base Voltage	V_{CBO}	-40	Vdc
Emitter - Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-600	mAdc

THERMAL CHARACTERISTICS

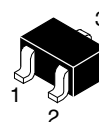
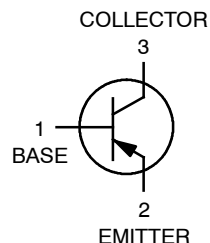
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



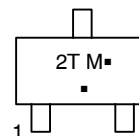
ON Semiconductor®

<http://onsemi.com>



SC-70
CASE 419
STYLE 3

MARKING DIAGRAM



2T = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT4403WT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector - Emitter Breakdown Voltage (Note 1) (I _C = -1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	-40	-	V _{dc}
Collector - Base Breakdown Voltage (I _C = -0.1 mA _{dc} , I _E = 0)	V _{(BR)CBO}	-40	-	V _{dc}
Emitter - Base Breakdown Voltage (I _E = -0.1 mA _{dc} , I _C = 0)	V _{(BR)EBO}	-5.0	-	V _{dc}
Base Cutoff Current (V _{CE} = -35 V _{dc} , V _{EB} = -0.4 V _{dc})	I _{BEV}	-	-0.1	μA _{dc}
Collector Cutoff Current (V _{CE} = -35 V _{dc} , V _{EB} = -0.4 V _{dc})	I _{CEX}	-	-0.1	μA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = -0.1 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -1.0 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -10 mA _{dc} , V _{CE} = -1.0 V _{dc}) (I _C = -150 mA _{dc} , V _{CE} = -2.0 V _{dc}) (Note 1) (I _C = -500 mA _{dc} , V _{CE} = -2.0 V _{dc}) (Note 1)	h _{FE}	30 60 100 100 20	- - - 300 -	-
Collector - Emitter Saturation Voltage (Note 1) (I _C = -150 mA _{dc} , I _B = -15 mA _{dc}) (I _C = -500 mA _{dc} , I _B = -50 mA _{dc})	V _{CE(sat)}	- -	-0.4 -0.75	V _{dc}
Base - Emitter Saturation Voltage (Note 1) (I _C = -150 mA _{dc} , I _B = -15 mA _{dc}) (I _C = -500 mA _{dc} , I _B = -50 mA _{dc})	V _{BE(sat)}	-0.75 -	-0.95 -1.3	V _{dc}

SMALL-SIGNAL CHARACTERISTICS

Current - Gain - Bandwidth Product (I _C = -20 mA _{dc} , V _{CE} = -10 V _{dc} , f = 100 MHz)	f _T	200	-	MHz
Collector-Base Capacitance (V _{CB} = -10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{cb}	-	8.5	pF
Emitter-Base Capacitance (V _{BE} = -0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{eb}	-	30	pF
Input Impedance (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{ie}	1.5	15	kΩ
Voltage Feedback Ratio (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{re}	0.1	8.0	X 10 ⁻⁴
Small - Signal Current Gain (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{fe}	60	500	-
Output Admittance (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{oe}	1.0	100	μmhos

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = -30 V _{dc} , V _{EB} = -2.0 V _{dc} , I _C = -150 mA _{dc} , I _{B1} = -15 mA _{dc})	t _d	-	15	ns
Rise Time		t _r	-	20	
Storage Time	(V _{CC} = -30 V _{dc} , I _C = -150 mA _{dc} , I _{B1} = I _{B2} = -15 mA _{dc})	t _s	-	225	ns
Fall Time		t _f	-	30	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUIT

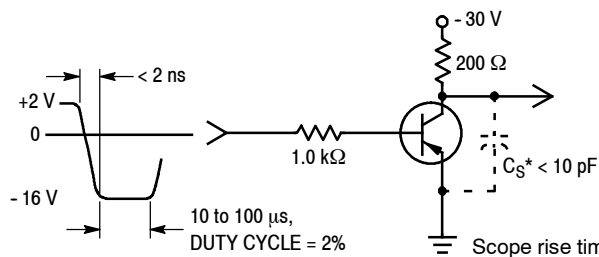


Figure 1. Turn-On Time

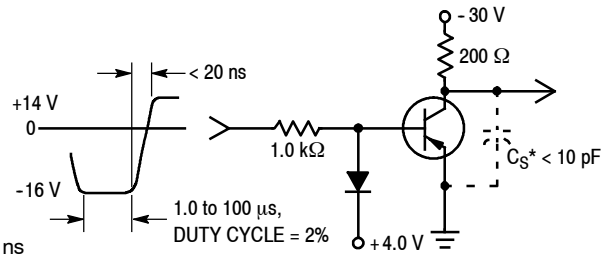


Figure 2. Turn-Off Time

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TRANSIENT CHARACTERISTICS

— 25°C - - 100°C

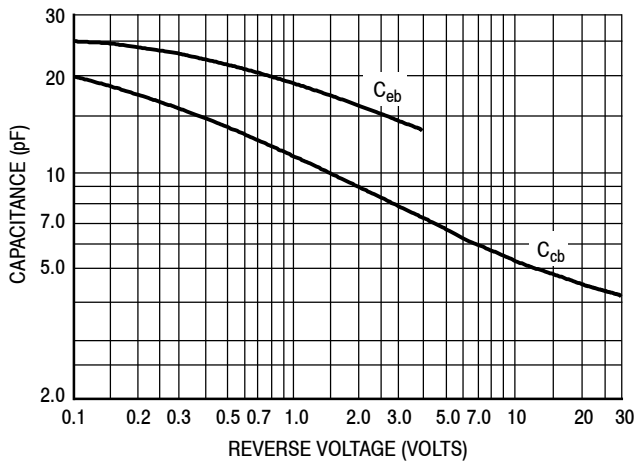


Figure 3. Capacitances

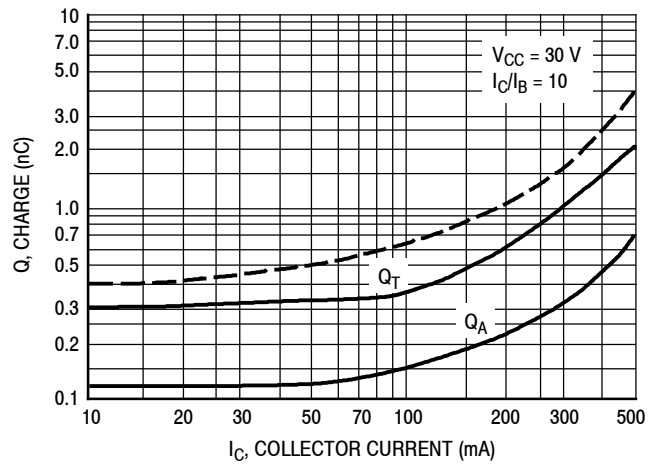


Figure 4. Charge Data

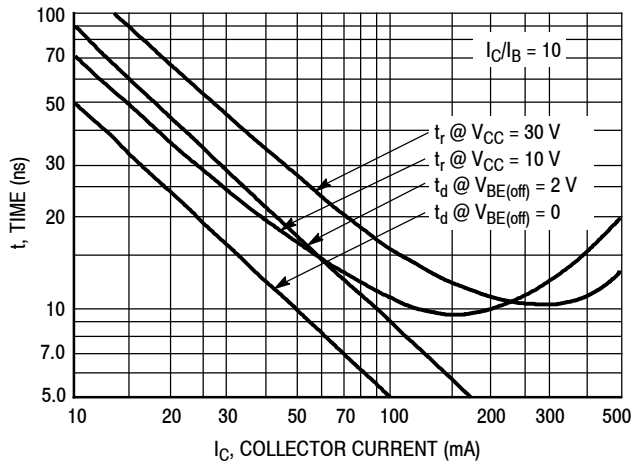


Figure 5. Turn-On Time

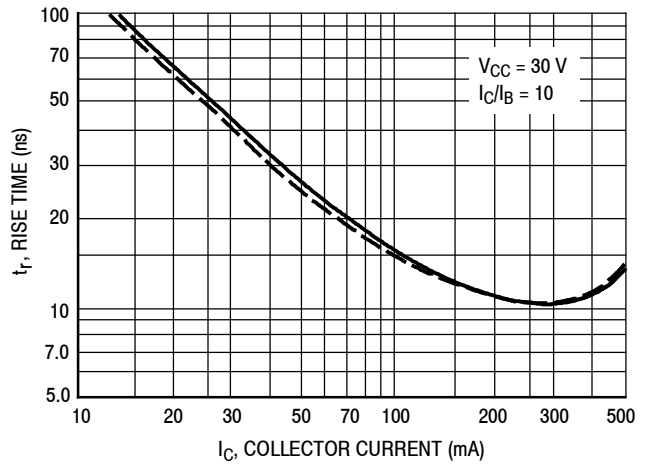


Figure 6. Rise Time

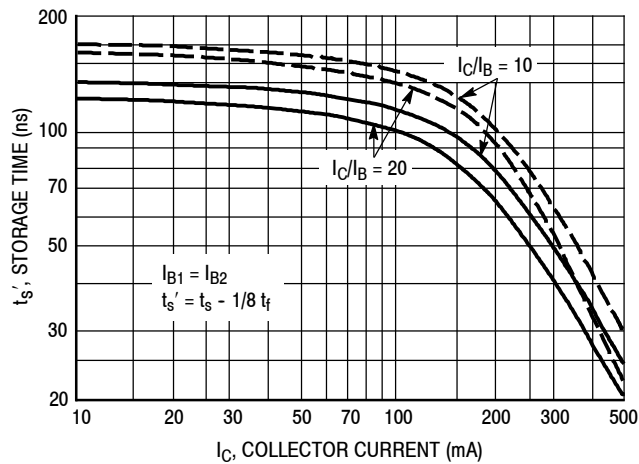


Figure 7. Storage Time

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SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$; Bandwidth = 1.0 Hz

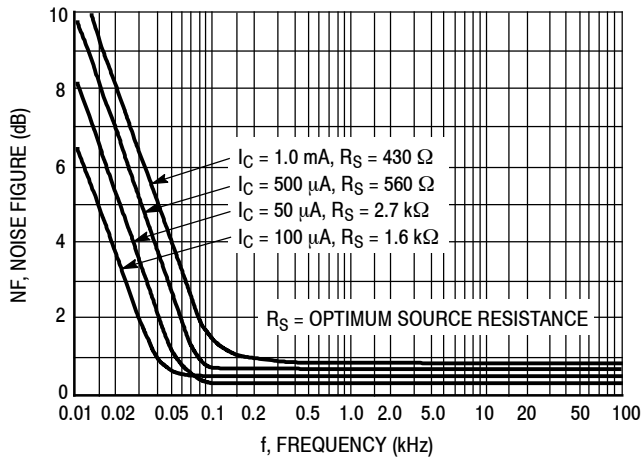


Figure 8. Frequency Effects

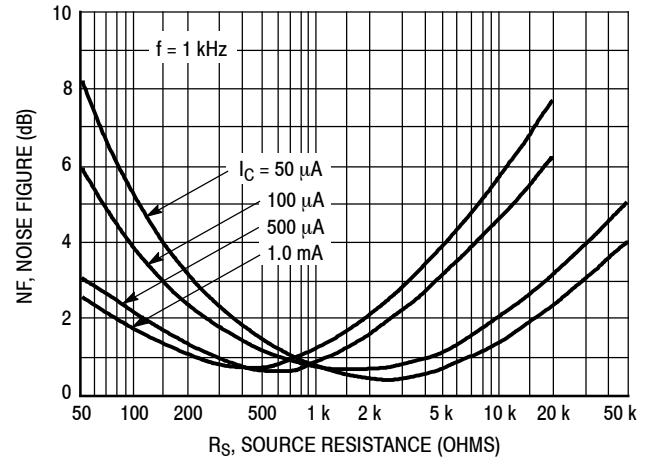


Figure 9. Source Resistance Effects

h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

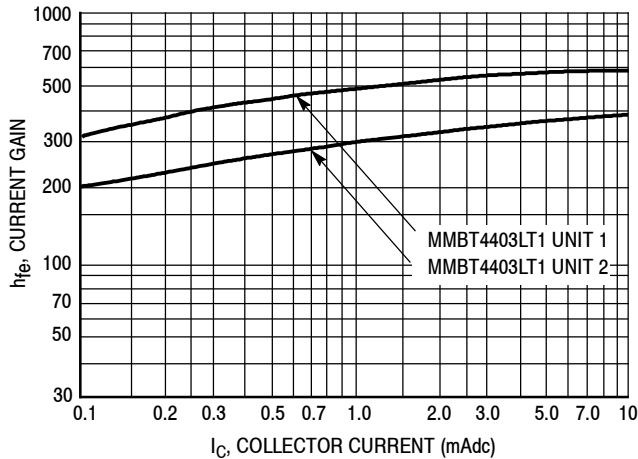


Figure 10. Current Gain

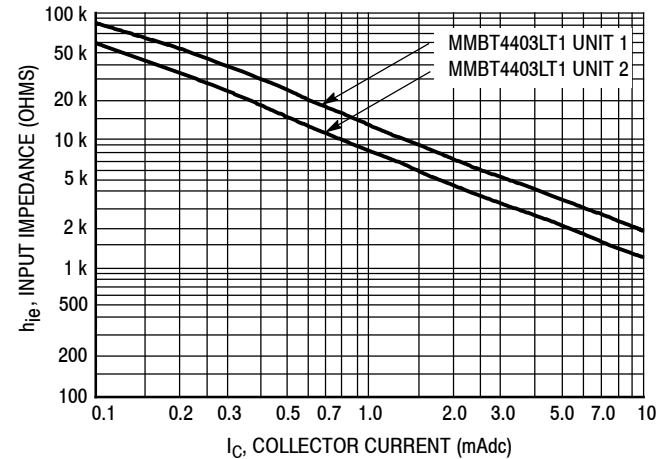


Figure 11. Input Impedance

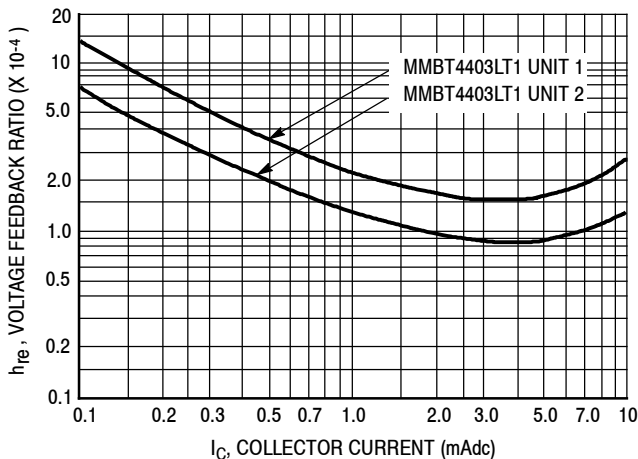


Figure 12. Voltage Feedback Ratio

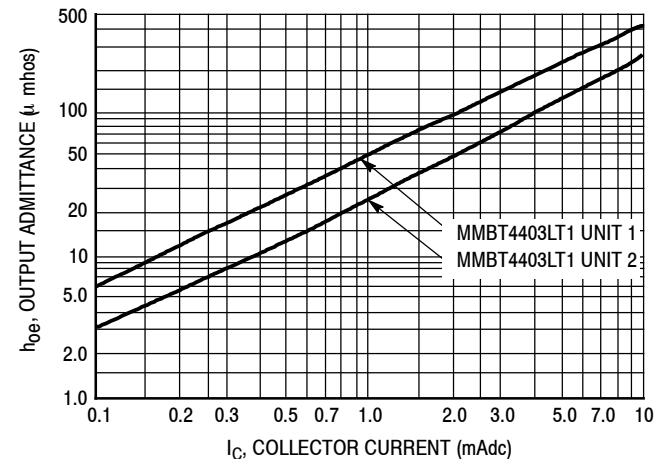


Figure 13. Output Admittance

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STATIC CHARACTERISTICS

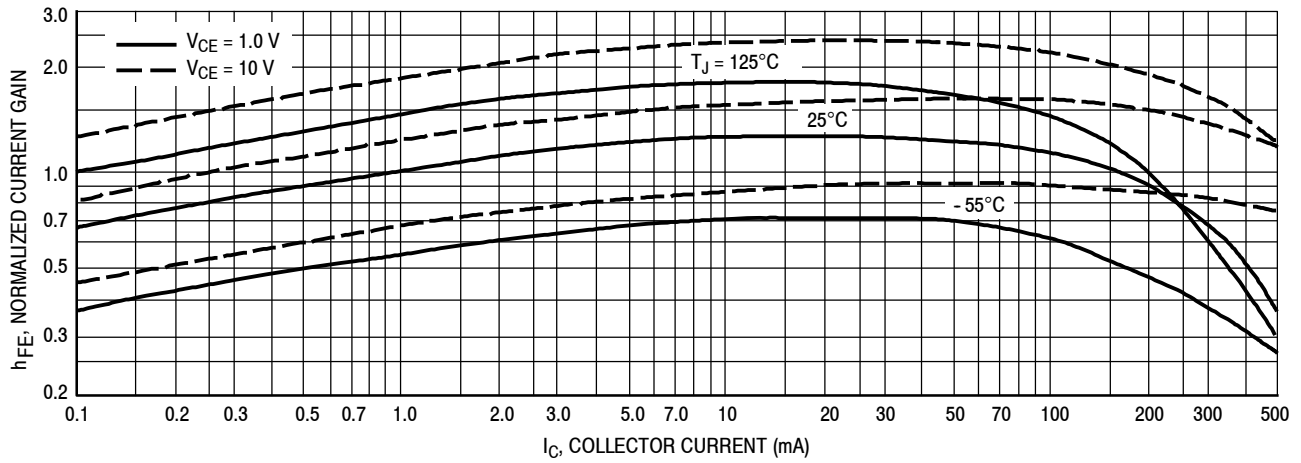


Figure 14. DC Current Gain

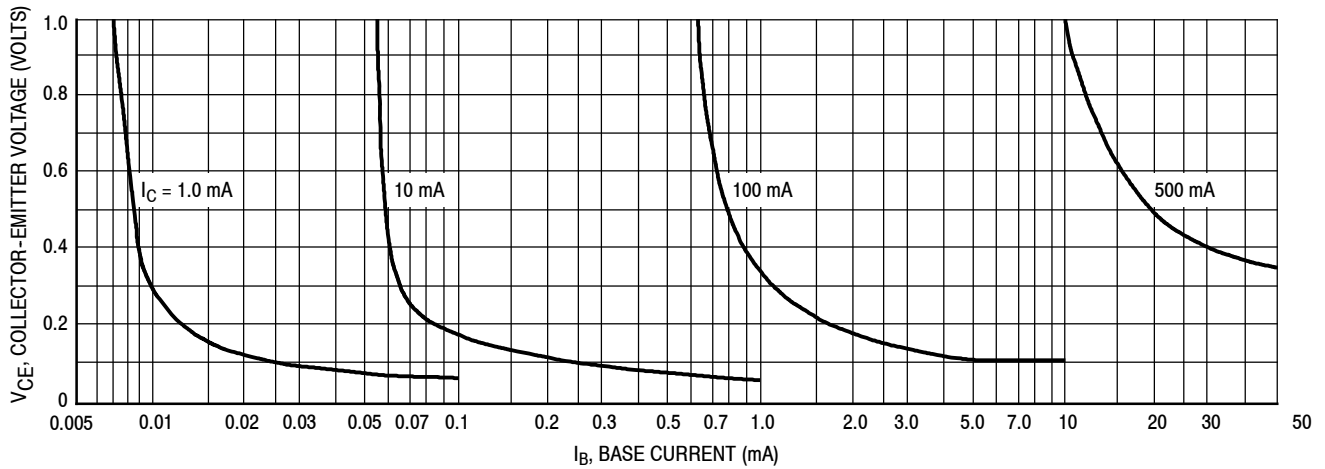


Figure 15. Collector Saturation Region

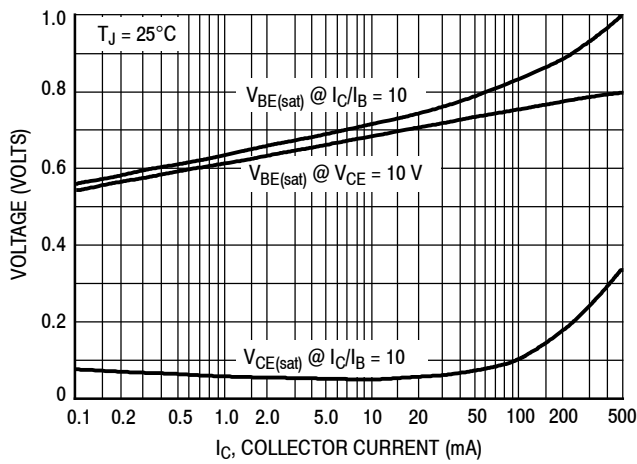


Figure 16. "On" Voltages

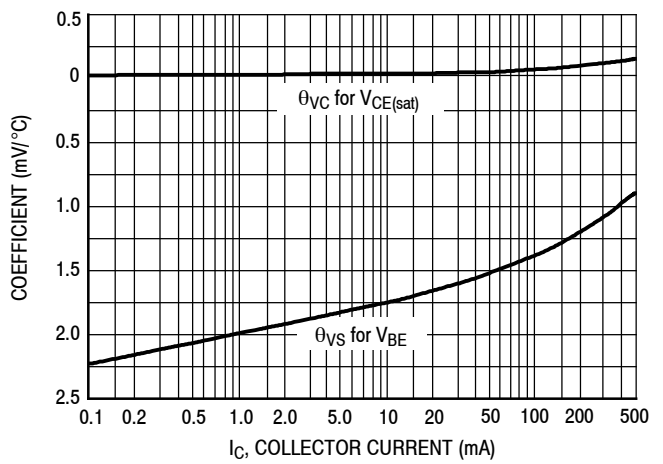
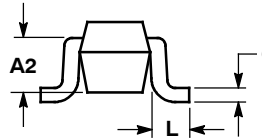
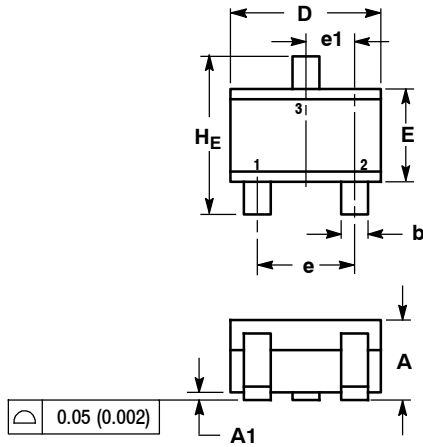


Figure 17. Temperature Coefficients

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PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N



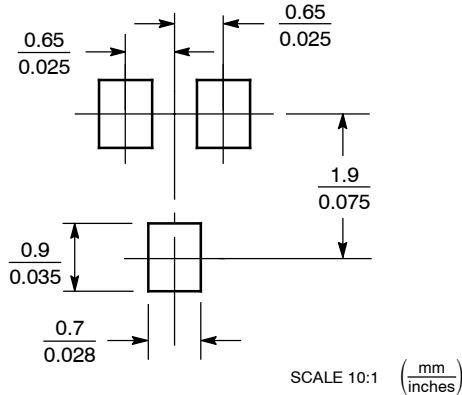
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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